

# MMBF4391LT1G, SMMBF4391LT1G, MMBF4392LT1G, MMBF4393LT1G



ON Semiconductor®

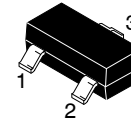
<http://onsemi.com>

## JFET Switching Transistors

### N-Channel

#### Features

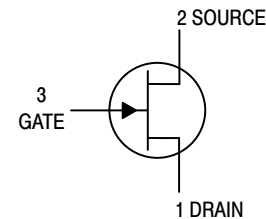
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*



SOT-23  
CASE 318  
STYLE 10

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	30	Vdc
Drain-Gate Voltage	$V_{DG}$	30	Vdc
Gate-Source Voltage	$V_{GS}$	30	Vdc
Forward Gate Current	$I_{G(f)}$	50	mAdc



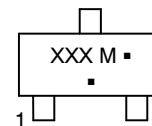
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

#### MARKING DIAGRAM



XXX = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### MARKING & ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 2 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MMBF4391LT1G, SMMBF4391LT1G, MMBF4392LT1G, MMBF4393LT1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Gate–Source Breakdown Voltage (I <sub>G</sub> = 1.0 μAdc, V <sub>DS</sub> = 0)	V <sub>(BR)GSS</sub>	30	–	Vdc
Gate Reverse Current (V <sub>GS</sub> = 15 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 25°C) (V <sub>GS</sub> = 15 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 100°C)	I <sub>GSS</sub>	– –	1.0 0.20	nAdc μAdc
Gate–Source Cutoff Voltage (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 10 nAdc) MMBF4391LT1, SMMBF4391LT1 MMBF4392LT1 MMBF4393LT1	V <sub>GS(off)</sub>	–4.0 –2.0 –0.5	–10 –5.0 –3.0	Vdc
Off–State Drain Current (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = –12 Vdc) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = –12 Vdc, T <sub>A</sub> = 100°C)	I <sub>D(off)</sub>	– –	1.0 1.0	nAdc μAdc
<b>ON CHARACTERISTICS</b>				
Zero–Gate–Voltage Drain Current (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0) MMBF4391LT1, SMMBF4391LT1 MMBF4392LT1 MMBF4393LT1	I <sub>DSS</sub>	50 25 5.0	150 75 30	mAdc
Drain–Source On–Voltage (I <sub>D</sub> = 12 mAdc, V <sub>GS</sub> = 0) MMBF4391LT1, SMMBF4391LT1 (I <sub>D</sub> = 6.0 mAdc, V <sub>GS</sub> = 0) MMBF4392LT1 (I <sub>D</sub> = 3.0 mAdc, V <sub>GS</sub> = 0) MMBF4393LT1	V <sub>DS(on)</sub>	– – –	0.4 0.4 0.4	Vdc
Static Drain–Source On–Resistance (I <sub>D</sub> = 1.0 mAdc, V <sub>GS</sub> = 0) MMBF4391LT1, SMMBF4391LT1 MMBF4392LT1 MMBF4393LT1	r <sub>DS(on)</sub>	– – –	30 60 100	Ω
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Input Capacitance (V <sub>DS</sub> = 0 Vdc, V <sub>GS</sub> = –15 Vdc, f = 1.0 MHz)	C <sub>iss</sub>	–	14	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 0 Vdc, V <sub>GS</sub> = –12 Vdc, f = 1.0 MHz)	C <sub>rss</sub>	–	3.5	pF

## ORDERING INFORMATION

Device	Marking	Package	Shipping <sup>†</sup>
MMBF4391LT1G	6J	SOT–23 (Pb–Free)	3,000 / Tape & Reel
SMMBF4391LT1G*	6J	SOT–23 (Pb–Free)	
MMBF4392LT1G	6K	SOT–23 (Pb–Free)	
MMBF4393LT1G	M6G	SOT–23 (Pb–Free)	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

TYPICAL CHARACTERISTICS

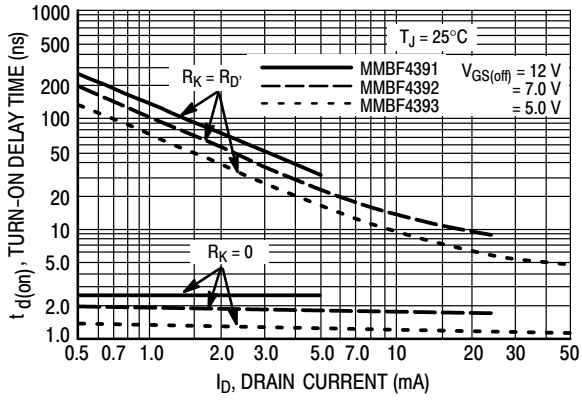


Figure 1. Turn-On Delay Time

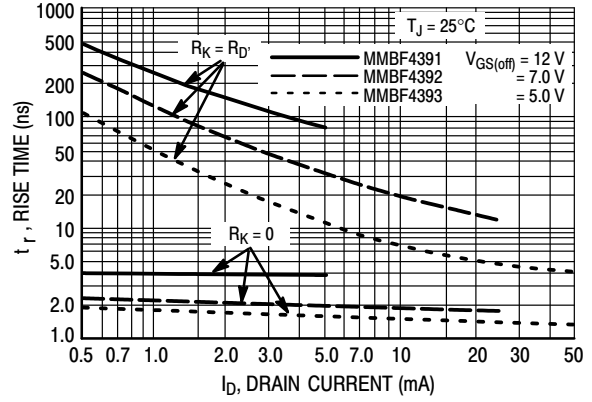


Figure 2. Rise Time

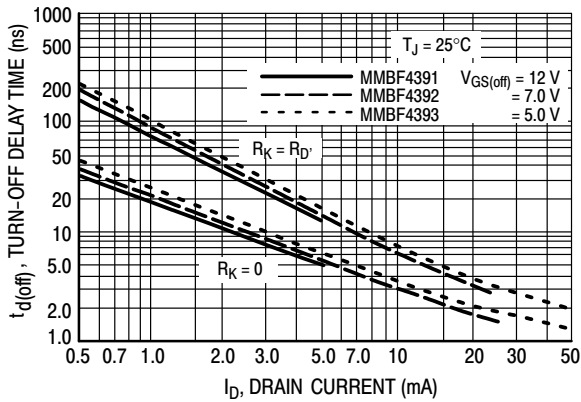


Figure 3. Turn-Off Delay Time

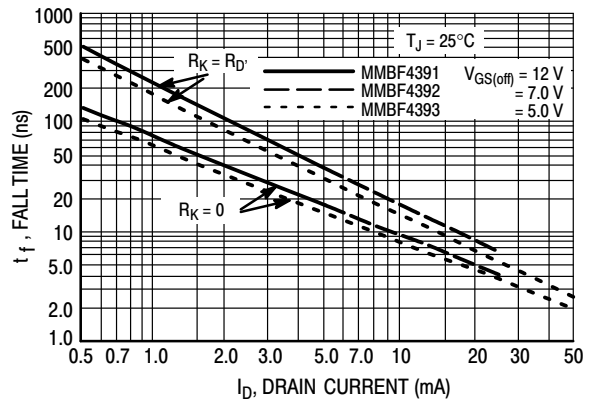


Figure 4. Fall Time

NOTE 1

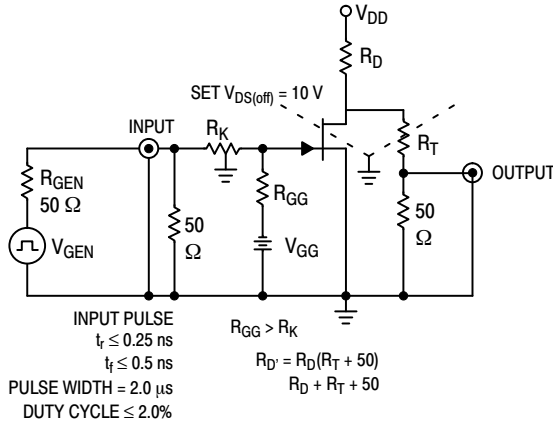


Figure 5. Switching Time Test Circuit

The switching characteristics shown above were measured using a test circuit similar to Figure 5. At the beginning of the switching interval, the gate voltage is at Gate Supply Voltage ( $-V_{GG}$ ). The Drain-Source Voltage ( $V_{DS}$ ) is slightly lower than Drain Supply Voltage ( $V_{DD}$ ) due to the voltage divider. Thus Reverse Transfer Capacitance ( $C_{rss}$ ) of Gate-Drain Capacitance ( $C_{gd}$ ) is charged to  $V_{GG} + V_{DS}$ .

During the turn-on interval, Gate-Source Capacitance ( $C_{gs}$ ) discharges through the series combination of  $R_{GEN}$  and  $R_K$ .  $C_{gd}$  must discharge to  $V_{DS(on)}$  through  $R_G$  and  $R_K$  in series with the parallel combination of effective load impedance ( $R'_D$ ) and Drain-Source Resistance ( $r_{DS}$ ). During the turn-off, this charge flow is reversed.

Predicting turn-on time is somewhat difficult as the channel resistance  $r_{DS}$  is a function of the gate-source voltage. While  $C_{gs}$  discharges,  $V_{GS}$  approaches zero and  $r_{DS}$  decreases. Since  $C_{gd}$  discharges through  $r_{DS}$ , turn-on time is non-linear. During turn-off, the situation is reversed with  $r_{DS}$  increasing as  $C_{gd}$  charges.

The above switching curves show two impedance conditions; 1)  $R_K$  is equal to  $R_D$ , which simulates the switching behavior of cascaded stages where the driving source impedance is normally the load impedance of the previous stage, and 2)  $R_K = 0$  (low impedance) the driving source impedance is that of the generator.

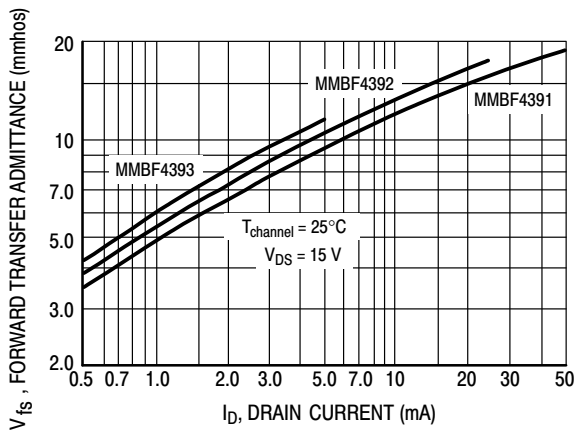


Figure 6. Typical Forward Transfer Admittance

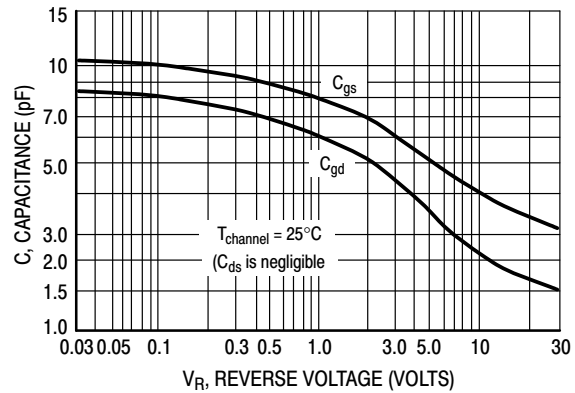


Figure 7. Typical Capacitance

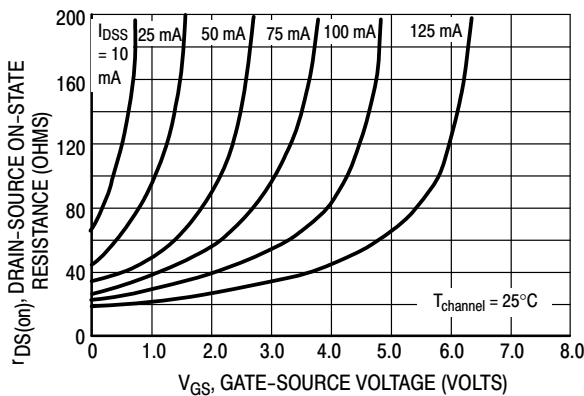


Figure 8. Effect of Gate-Source Voltage on Drain-Source Resistance

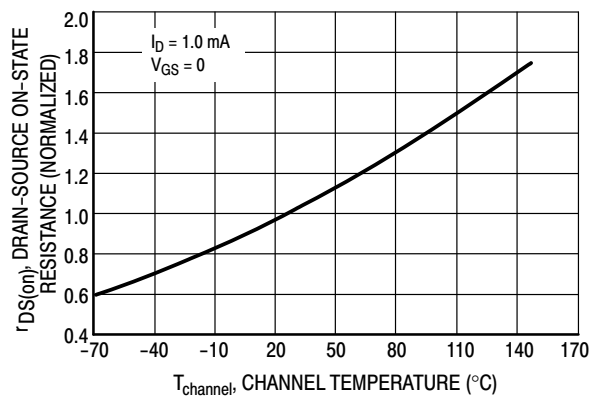


Figure 9. Effect of Temperature on Drain-Source On-State Resistance

**NOTE 2**

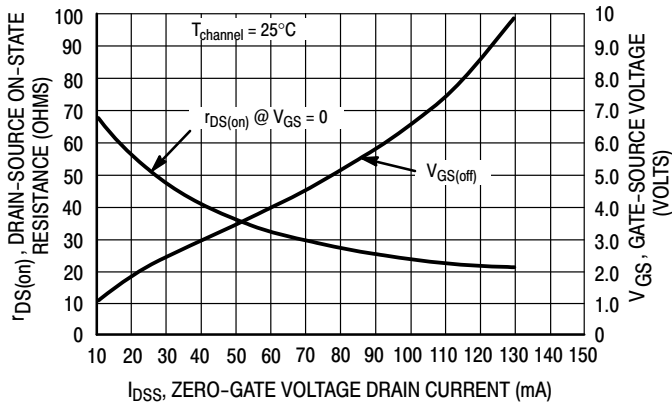
The Zero-Gate-Voltage Drain Current ( $I_{DSS}$ ) is the principle determinant of other J-FET characteristics. Figure 10 shows the relationship of Gate-Source Off Voltage ( $V_{GS(off)}$ ) and Drain-Source On Resistance ( $r_{DS(on)}$ ) to  $I_{DSS}$ . Most of the devices will be within  $\pm 10\%$  of the values shown in Figure 10. This data will be useful in predicting the characteristic variations for a given part number.

For example:

Unknown

$r_{DS(on)}$  and  $V_{GS}$  range for an MMBF4392

The electrical characteristics table indicates that an MMBF4392 has an  $I_{DSS}$  range of 25 to 75 mA. Figure 10 shows  $r_{DS(on)} = 52 \Omega$  for  $I_{DSS} = 25$  mA and  $30 \Omega$  for  $I_{DSS} = 75$  mA. The corresponding  $V_{GS}$  values are 2.2 V and 4.8 V.

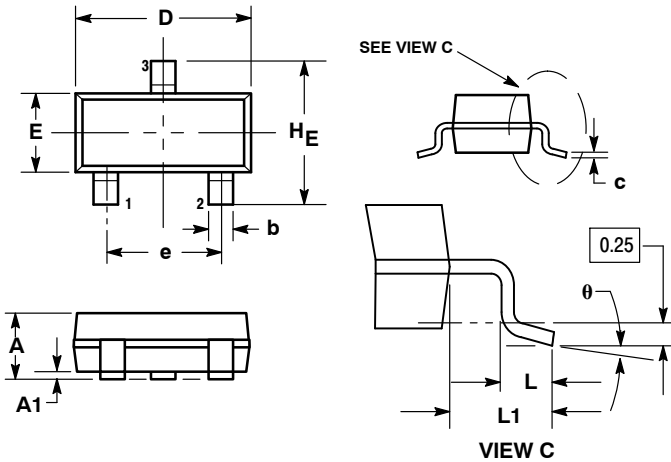


**Figure 10. Effect of  $I_{DSS}$  on Drain-Source Resistance and Gate-Source Voltage**

# MMBF4391LT1G, SMMBF4391LT1G, MMBF4392LT1G, MMBF4393LT1G

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AP



NOTES:

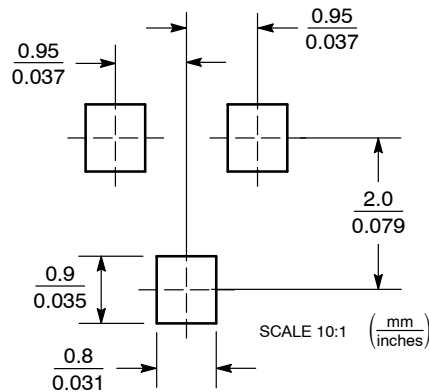
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 10:

1. DRAIN
2. SOURCE
3. GATE

### SOLDERING FOOTPRINT



ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

**LITERATURE FULFILLMENT:**  
Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
Email: orderlit@onsemi.com

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>  
For additional information, please contact your local Sales Representative



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.